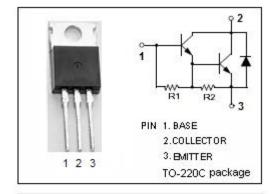


isc Silicon NPN Darlington Power Transistor

2SC4350

DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)}= 100V(Min)
- · High DC Current Gain
 - : h_{FE} = 2000~20000(Min) @I_C= 5A
- · Fast Switching Speed
- · Good Linearity of hFE
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

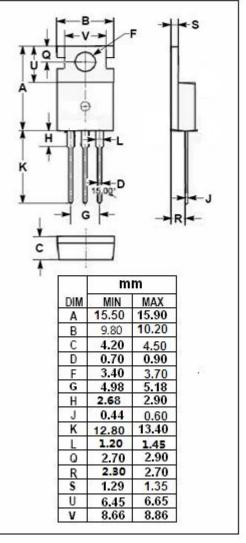


APPLICATIONS

 Designed for high-precision control such as PWM control for pulse motors or brushless motors in OA and FA equipment.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	100	V	
V _{CEO}	Collector-Emitter Voltage	100	V	
V _{EBO}	Emitter-Base Voltage	7	V	
Ic	Collector Current-Continuous	10	А	
lв	Base Current-Continuous	0.5	А	
Pc	Collector Power Dissipation @ Ta=25℃	1.5	W	
	Collector Power Dissipation @ T _C =25°C	40		
TJ	Junction Temperature	e 150		
T _{stg}	Storage Temperature Range	-55~150 ℃		





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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
Collector-Emitter Sustaining Voltage	I _C = 0.1A; I _B = 0	100			V
Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	100			V
Emitter-Base Breakdown Voltage	I _E = 5mA; I _C = 0	7			V
Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 5mA			1.5	V
Base-Emitter Saturation Voltage	I _C = 5A; I _B = 5mA			2.0	V
Collector Cutoff Current	V _{CB} = 100V; I _E = 0			1	μА
Emitter Cutoff Current	V _{EB} = 7V; I _C =			5.0	mA
DC Current Gain	I _C = 5A; V _{CE} = 2V	2000		20000	
	Collector-Emitter Sustaining Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage Collector Cutoff Current Emitter Cutoff Current	Collector-Emitter Sustaining Voltage I_{C} = 0.1A; I_{B} = 0Collector-Base Breakdown Voltage I_{C} = 1mA; I_{E} = 0Emitter-Base Breakdown Voltage I_{E} = 5mA; I_{C} = 0Collector-Emitter Saturation Voltage I_{C} = 5A; I_{B} = 5mABase-Emitter Saturation Voltage I_{C} = 5A; I_{B} = 5mACollector Cutoff Current V_{CB} = 100V; I_{E} = 0Emitter Cutoff Current V_{EB} = 7V; I_{C} =	Collector-Emitter Sustaining Voltage I_{C} = 0.1A; I_{B} = 0100Collector-Base Breakdown Voltage I_{C} = 1mA; I_{E} = 0100Emitter-Base Breakdown Voltage I_{E} = 5mA; I_{C} = 07Collector-Emitter Saturation Voltage I_{C} = 5A; I_{B} = 5mABase-Emitter Saturation Voltage I_{C} = 5A; I_{B} = 5mACollector Cutoff Current V_{CB} = 100V; I_{E} = 0Emitter Cutoff Current V_{EB} = 7V; I_{C} =	Collector-Emitter Sustaining Voltage I_{c} = 0.1A; I_{B} = 0100Collector-Base Breakdown Voltage I_{C} = 1mA; I_{E} = 0100Emitter-Base Breakdown Voltage I_{E} = 5mA; I_{C} = 07Collector-Emitter Saturation Voltage I_{C} = 5A; I_{B} = 5mABase-Emitter Saturation Voltage I_{C} = 5A; I_{B} = 5mACollector Cutoff Current V_{CB} = 100V; I_{E} = 0Emitter Cutoff Current V_{EB} = 7V; I_{C} =	Collector-Emitter Sustaining Voltage $I_C=0.1A$; $I_B=0$ 100Collector-Base Breakdown Voltage $I_C=1mA$; $I_C=0$ 100Emitter-Base Breakdown Voltage $I_C=5mA$; $I_C=0$ 7Collector-Emitter Saturation Voltage $I_C=5A$; $I_B=5mA$ 1.5Base-Emitter Saturation Voltage $I_C=5A$; $I_B=5mA$ 2.0Collector Cutoff Current $V_{CB}=100V$; $I_C=0$ 1Emitter Cutoff Current $V_{CB}=7V$; $I_C=0$ 5.0

Switching times

t _{on}	Turn-on Time		0.4	μS
t _{stg}	Storage Time	$egin{array}{ll} I_{C}\!=5A,I_{B1}\!=-I_{B2}\!=5mA \ R_{L}\!=10\Omega;V_{CC}\!pprox50V \end{array}$	2.5	μS
t _f	Fall Time		0.7	μS

♦ h_{FE} Classifications

М	L	К
2000-5000	4000-10000	8000-20000

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